

/ Descriptions

TO-126F

NPN

Silicon NPN transistor in a TO-126F Plastic Package.

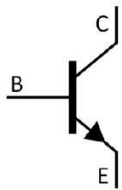
/ Features

KSE350

High collector-Emitter breakdown voltage Suitable for transformer complement to KSE350.

/ Applications

High voltage general purpose applications.

/ Equivalent Circuit**/ Pinning**

PIN1 Emitter

PIN 2 Collector

PIN 3 Base

/ h_{FE} Classifications & Marking

See Marking Instructions.

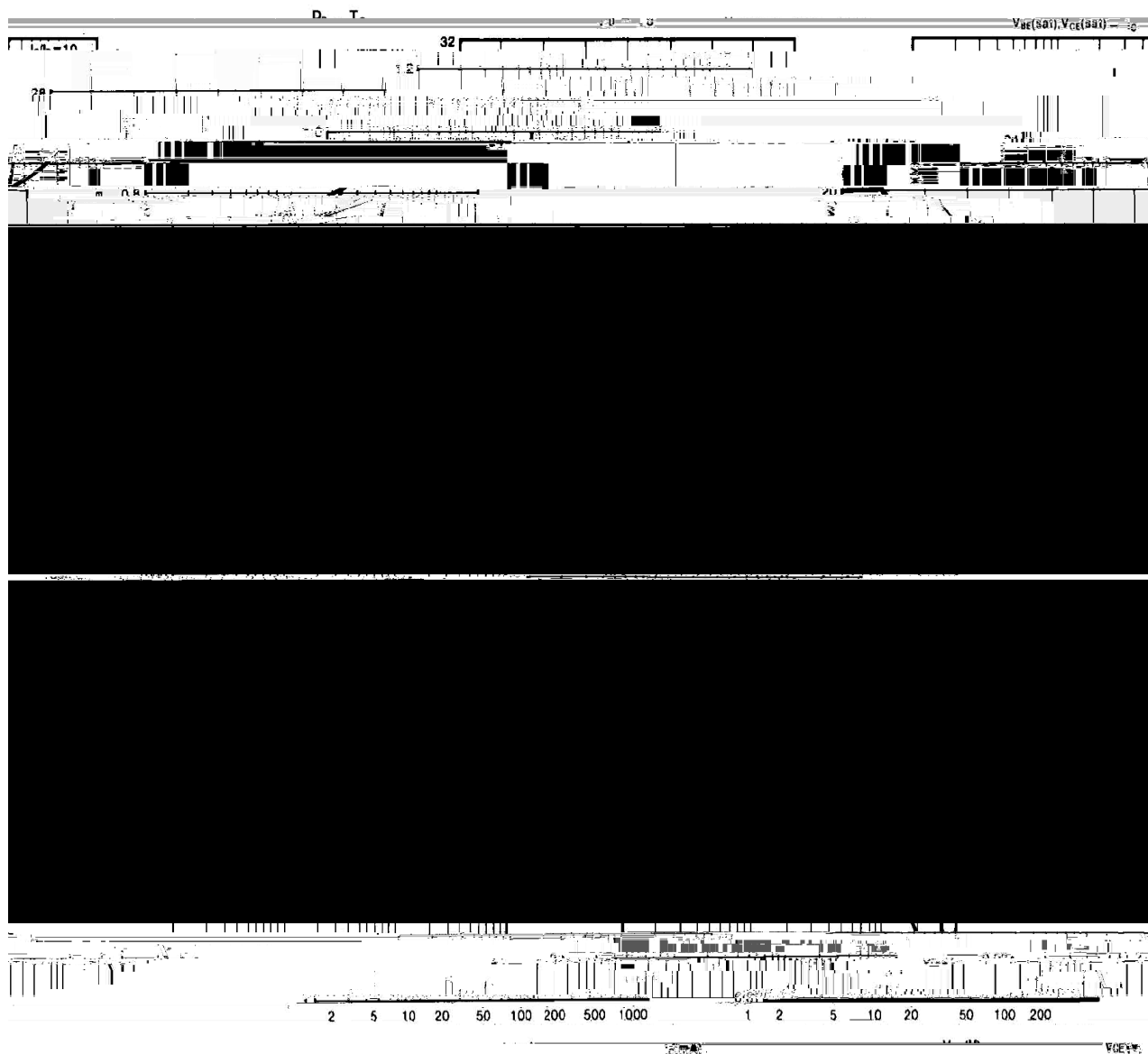
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	300	V
Collector to Emitter Voltage	V_{CEO}	300	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current – Continuous	I_C	500	mA
Collector Power Dissipation	$P_{C(Tc=25)}$	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

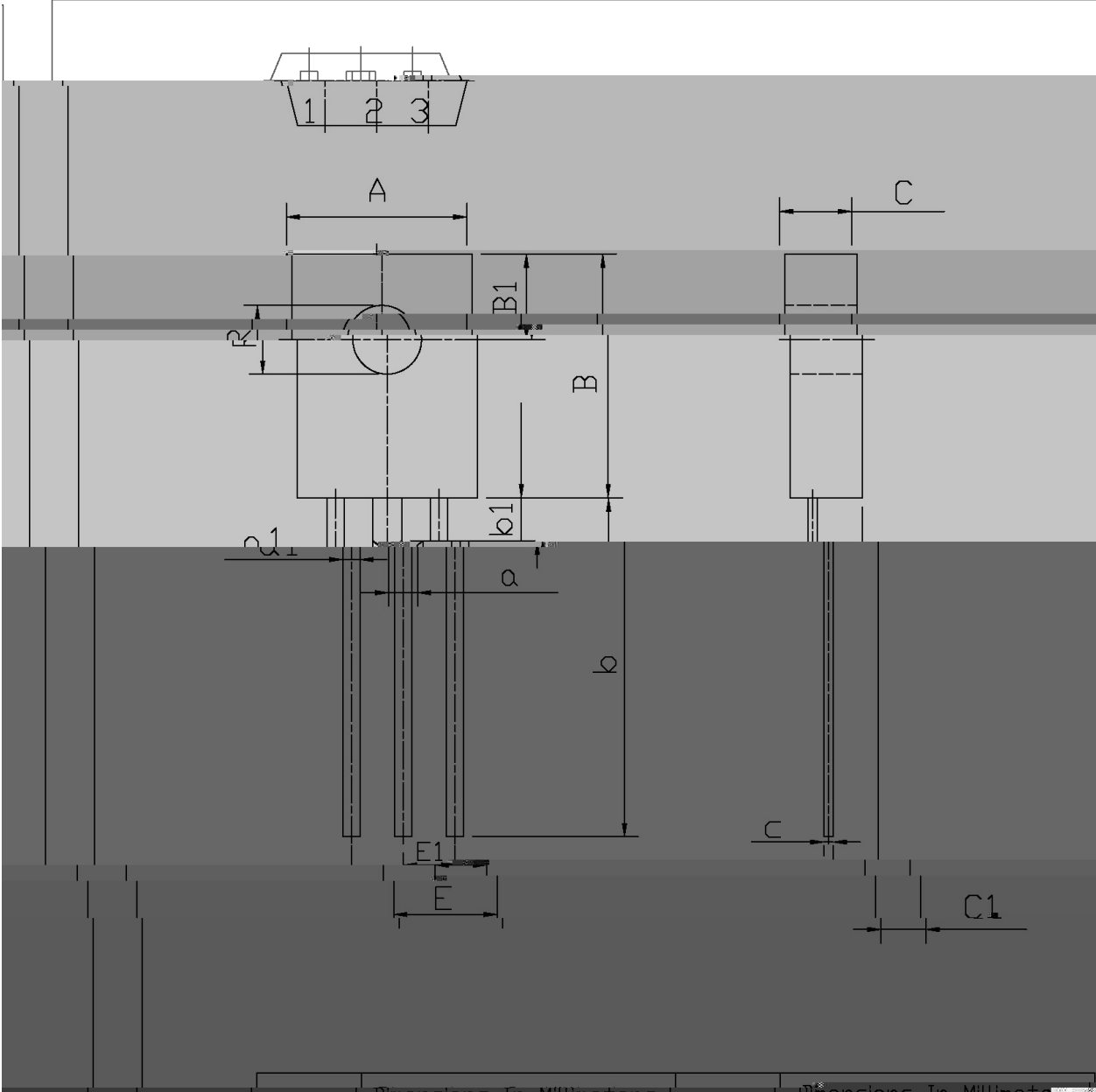
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=0.1mA$ $I_E=0$	300			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	300			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=0.1mA$ $I_C=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=300V$ $I_E=0$			100	μA
Emitter Cut-off Current	I_{EBO}	$V_{BE}=3.0V$ $I_C=0$			100	μA
DC Current Gain	h_{FE}	$V_{CE}=10V$ $I_C=50mA$	30		240	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=50mA$ $I_B=5mA$			1.0	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=50mA$ $I_B=5mA$			1.2	V

/ Electrical Characteristic Curve



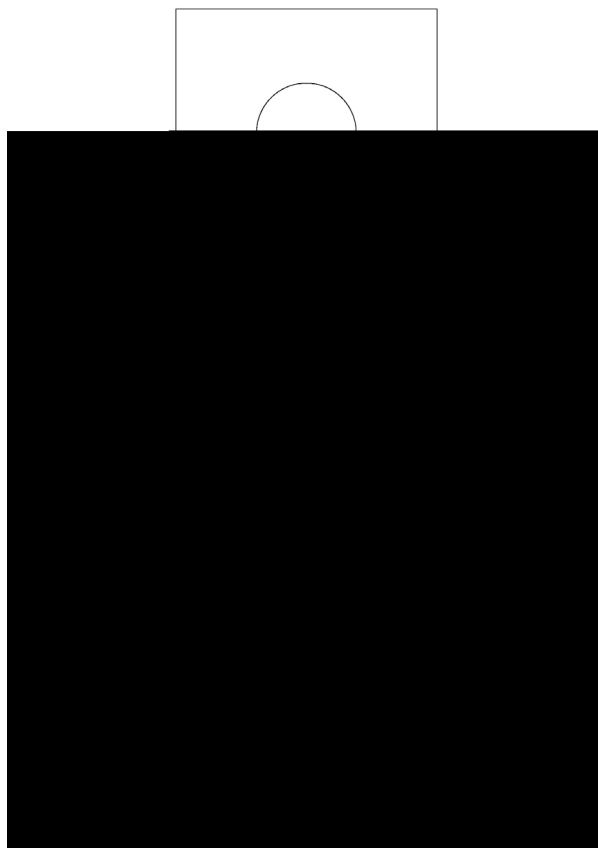
/ Package Dimensions

单位: mm



Symbol	Min	Max	Symbol	Min	Max
A	7.8	8.2	a1	0.65	0.86

/ Marking Instructions



BR

KSE340

Note:

BR: Company Code

KSE340: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note: